



# NPN SILICON RF TRANSISTOR

# NE68719

## NPN EPITAXIAL SILICON RF TRANSISTOR FOR LOW-NOISE MICROWAVE AMPLIFICATION 3-PIN ULTRA SUPER MINIMOLD

### FEATURES

- Low noise  
NF = 1.3 dB TYP. @  $V_{CE} = 2\text{ V}$ ,  $I_C = 3\text{ mA}$ ,  $f = 2\text{ GHz}$   
NF = 1.3 dB TYP. @  $V_{CE} = 1\text{ V}$ ,  $I_C = 3\text{ mA}$ ,  $f = 2\text{ GHz}$
- 3-pin ultra super minimold package

### ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NE68719-A	50 pcs (Non reel)	• 8 mm wide embossed taping • Pin 3 (collector) face the perforation side of the tape
NE68719-T1-A	3 kpcs/reel	

**Remark** To order evaluation samples, contact your nearby sales office.  
The unit sample quantity is 50 pcs.

### ABSOLUTE MAXIMUM RATINGS ( $T_A = +25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	$V_{CBO}$	5	V
Collector to Emitter Voltage	$V_{CEO}$	3	V
Emitter to Base Voltage	$V_{EBO}$	2	V
Collector Current	$I_C$	30	mA
Total Power Dissipation	$P_{tot}$ <sup>Note</sup>	90	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$

**Note** Free air

**Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge**

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25°C)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
<b>DC Characteristics</b>						
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> = 5 V, I <sub>E</sub> = 0 mA	–	–	100	nA
Emitter Cut-off Current	I <sub>EB0</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0 mA	–	–	100	nA
DC Current Gain	h <sub>FE</sub> <sup>Note 1</sup>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 20 mA	70	–	140	–
<b>RF Characteristics</b>						
Gain Bandwidth Product (1)	f <sub>T</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 20 mA, f = 2 GHz	9	11	–	GHz
Gain Bandwidth Product (2)	f <sub>T</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 10 mA, f = 2 GHz	7	9	–	GHz
Insertion Power Gain (1)	S <sub>21e</sub>   <sup>2</sup>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 20 mA, f = 2 GHz	8.5	10	–	dB
Insertion Power Gain (2)	S <sub>21e</sub>   <sup>2</sup>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 10 mA, f = 2 GHz	6.0	7.5	–	dB
Noise Figure (1)	NF	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 3 mA, f = 2 GHz	–	1.3	2.0	dB
Noise Figure (2)	NF	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 3 mA, f = 2 GHz	–	1.3	2.0	dB
Reverse Transfer Capacitance	C <sub>re</sub> <sup>Note 2</sup>	V <sub>CB</sub> = 2 V, I <sub>E</sub> = 0 mA, f = 1 MHz	–	0.4	0.8	pF

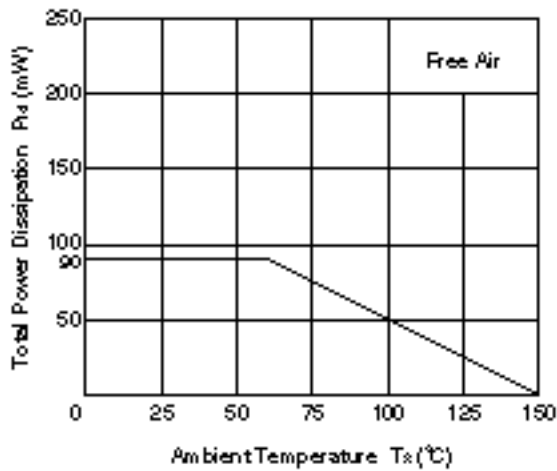
- Notes 1.** Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%  
**2.** Collector to base capacitance when the emitter grounded

**h<sub>FE</sub> CLASSIFICATION**

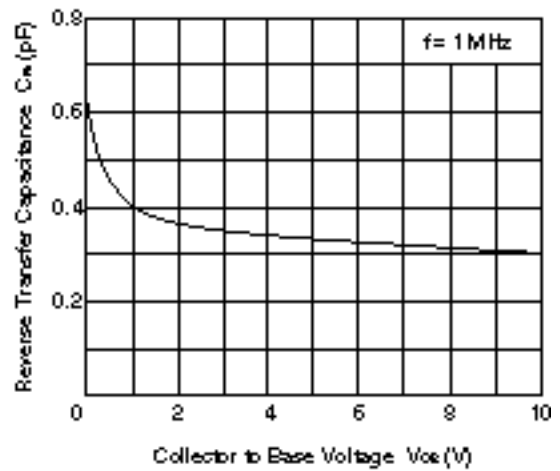
Rank	FB
Marking	86
h <sub>FE</sub> Value	70 to 140

• TYPICAL CHARACTERISTICS ( $T_A = +25^\circ\text{C}$ , unless otherwise specified)

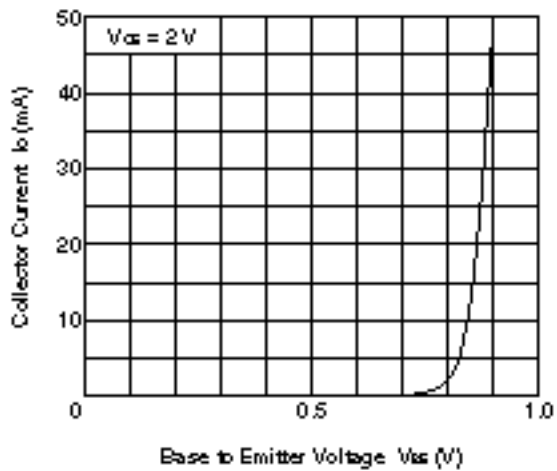
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



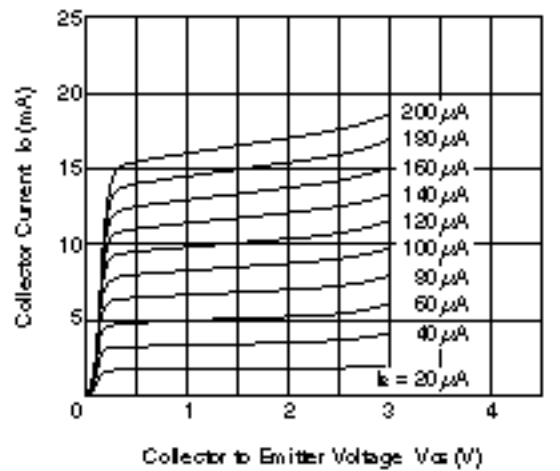
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



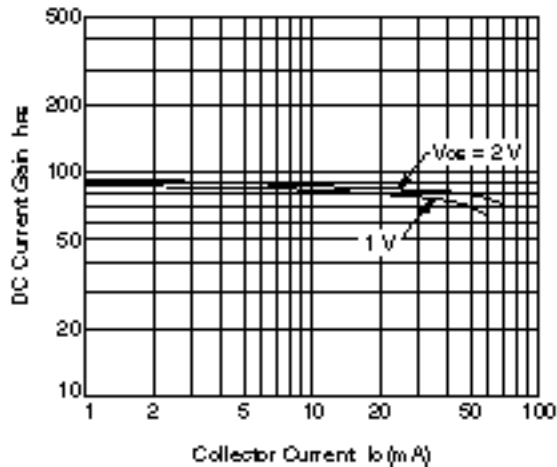
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



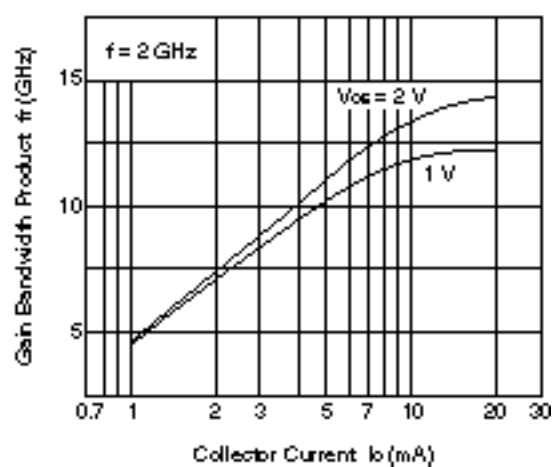
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

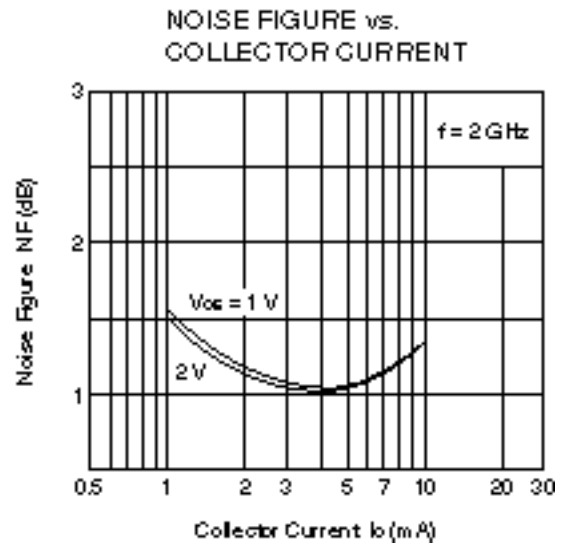
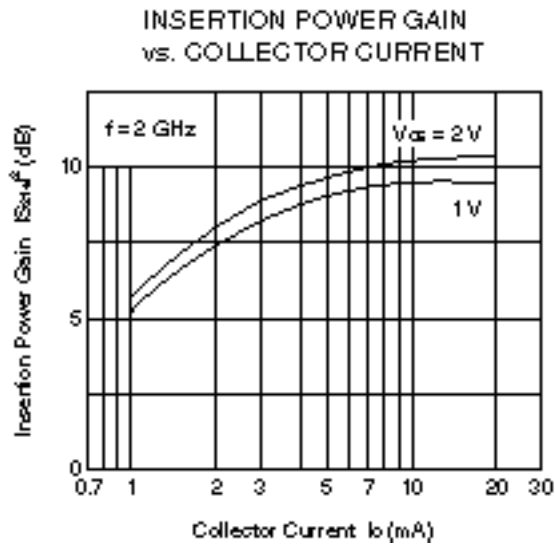


DC CURRENT GAIN vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT





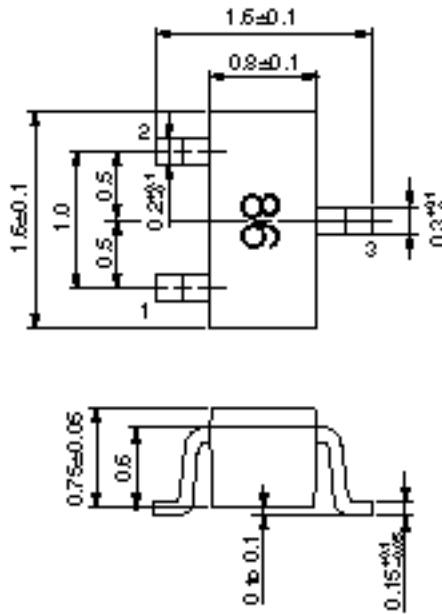
**Remark** The graphs indicate nominal characteristics.

**S-PARAMETERS**

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- Click here to download S-parameters.
- [RF and Microwave] @ [Device Parameters]
- URL <http://www.necel.com/microwave/en/>

**PACKAGE DIMENSIONS**

**3-PIN ULTRA SUPER MINIMOLD (UNIT: mm)**



**PIN CONNECTIONS**

- 1. Emitter
- 2. Base
- 3. Collector